

XC7WH14

Inverting Schmitt trigger

Rev. 01 — 7 September 2009

Product data sheet

1. General description

The XC7WH14 is a high-speed Si-gate CMOS device. This device provides an inverting buffer function with Schmitt trigger action. This device is capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

2. Features

- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Applications

- Wave and pulse shaper for highly noisy environment
- Astable multivibrator
- Monostable multivibrator

4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
XC7WH14DP	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
XC7WH14DC	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
XC7WH14GD	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5\text{ mm}$	SOT996-2

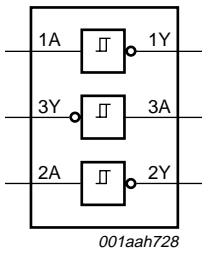
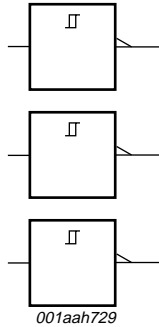
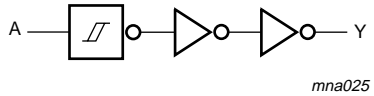
5. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
XC7WH14DP	f14
XC7WH14DC	f14
XC7WH14GD	f14

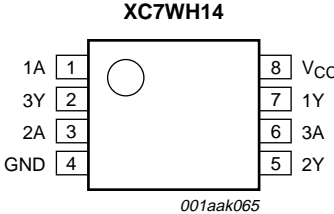
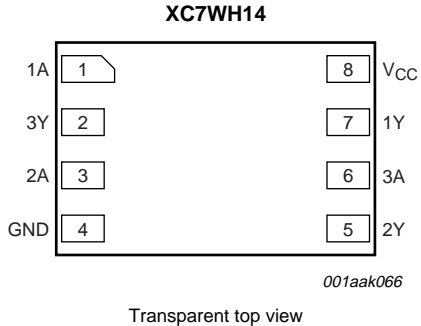
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

6. Functional diagram

 <p>Fig 1. Logic symbol</p>	 <p>Fig 2. IEC logic symbol</p>	 <p>Fig 3. Logic diagram (one Schmitt trigger)</p>
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7. Pinning information

7.1 Pinning

 <p>Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)</p>	 <p>Fig 5. Pin configuration SOT996-2 (XSON8U)</p>
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7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A, 3A	1, 3, 6	data input
GND	4	ground (0 V)
1Y, 2Y, 3Y	7, 5, 2	data output
V _{CC}	8	supply voltage

8. Functional description

Table 4. Function table [1]

Input nA	Output nY
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
V _I	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V	-20	-	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	[1] -	±20	mA
I _O	output current	-0.5 V < V _O < V _{CC} + 0.5 V	-	±25	mA
I _{CC}	supply current		-	75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly at 2.5 mW/K.
 For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly at 8 mW/K.
 For XSON8U package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C

11. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V_{OH}	HIGH-level output voltage	$V_I = V_{T+}$ or V_{T-}								
		$I_O = -50 \mu\text{A}$; $V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu\text{A}$; $V_{CC} = 3.0 \text{ V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu\text{A}$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_O = -8.0 \text{ mA}$; $V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}								
		$I_O = 50 \mu\text{A}$; $V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu\text{A}$; $V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu\text{A}$; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_O = 8.0 \text{ mA}$; $V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	$V_I = 5.5 \text{ V}$ or GND; $V_{CC} = 0 \text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μA
C_I	input capacitance		-	1.5	10	-	10	-	10	pF

11.1 Transfer characteristics

Table 8. Transfer characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V). See [Figure 8](#) and [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{T+}	positive-going threshold voltage	V _{CC} = 3.0 V	-	-	2.2	-	2.2	-	2.2	V
		V _{CC} = 4.5 V	-	-	3.15	-	3.15	-	3.15	V
		V _{CC} = 5.5 V	-	-	3.85	-	3.85	-	3.85	V
V _{T-}	negative-going threshold voltage	V _{CC} = 3.0 V	0.9	-	-	0.9	-	0.9	-	V
		V _{CC} = 4.5 V	1.35	-	-	1.35	-	1.35	-	V
		V _{CC} = 5.5 V	1.65	-	-	1.65	-	1.65	-	V
V _H	hysteresis voltage	V _{CC} = 3.0 V	0.3	-	1.2	0.3	1.2	0.25	1.2	V
		V _{CC} = 4.5 V	0.4	-	1.4	0.4	1.4	0.35	1.4	V
		V _{CC} = 5.5 V	0.5	-	1.6	0.5	1.6	0.45	1.6	V

12. Dynamic characteristics

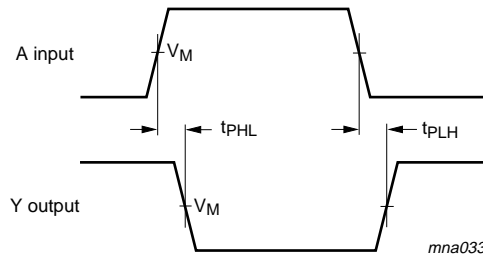
Table 9. Dynamic characteristics

GND = 0 V; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t _{pd}	propagation delay	nA to nY; see Figure 6 [1]								
		V _{CC} = 3.0 V to 3.6 V [2]								
		C _L = 15 pF	-	4.2	12.8	1.0	15.0	1.0	16.5	ns
		C _L = 50 pF	-	6.0	16.3	1.0	18.5	1.0	20.5	ns
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	-	3.2	8.6	1.0	10.0	1.0	11.0	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC}	-	10	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [2] Typical values are measured at V_{CC} = 3.3 V.
- [3] Typical values are measured at V_{CC} = 5.0 V.
- [4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

13. Waveforms

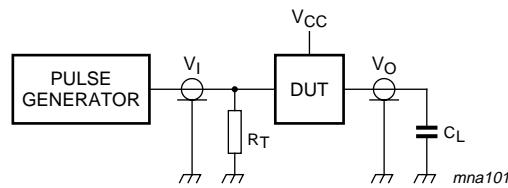


Measurement points are given in [Table 10](#).

Fig 6. The input (nA) to output (nY) propagation delays

Table 10. Measurement points

Type number	Input		Output
	V _I	V _M	V _M
XC7WH14	GND to V _{CC}	0.5 × V _{CC}	0.5 × V _{CC}



Test data is given in [Table 11](#).

Definitions for test circuit:

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 7. Load circuitry for switching times

Table 11. Test data

Type	Input		Load	Test
	V _I	t _r , t _f	C _L	
XC7WH14	V _{CC}	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

13.1 Transfer characteristic waveforms

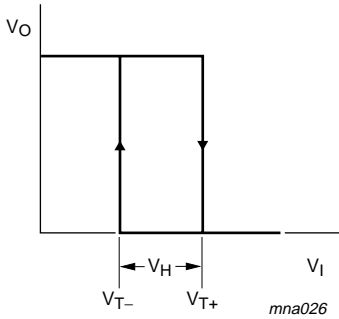


Fig 8. Transfer characteristic

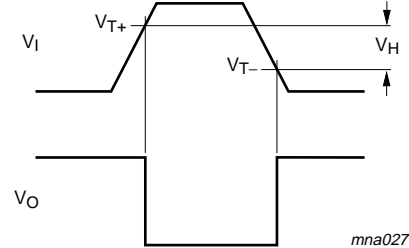
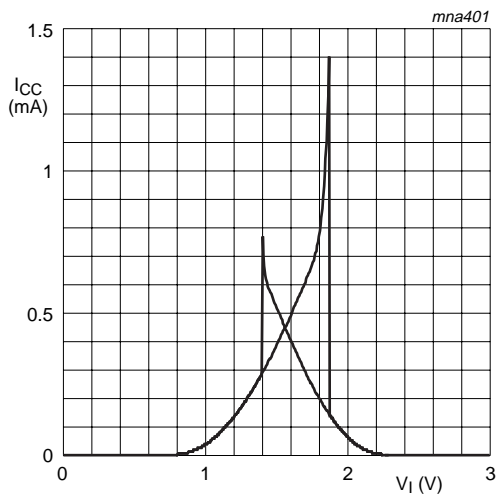
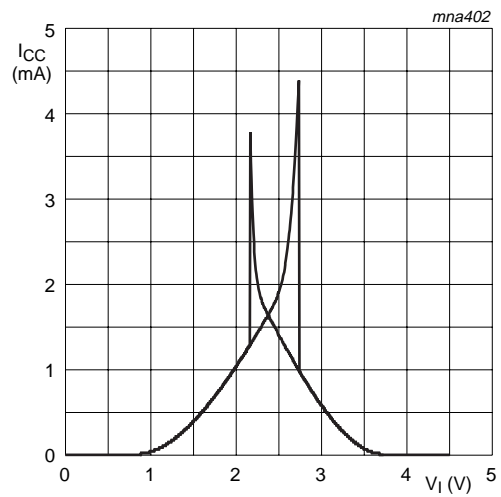


Fig 9. The definitions of V_{T+} , V_{T-} and V_H



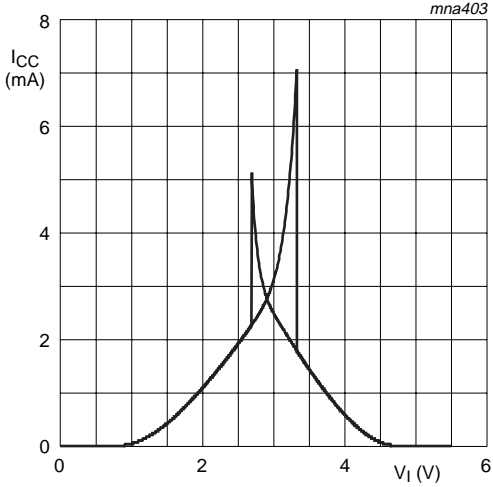
$V_{CC} = 3.0\text{ V}$.

Fig 10. Typical transfer characteristics



$V_{CC} = 4.5\text{ V}$.

Fig 11. Typical transfer characteristics



$V_{CC} = 5.5$ V.

Fig 12. Typical transfer characteristics

14. Application information

The slow input rise and fall times cause additional power dissipation, which can be calculated using the following formula:

$$P_{\text{add}} = f_i \times (t_r \times \Delta I_{\text{CC(AV)}} + t_f \times \Delta I_{\text{CC(AV)}}) \times V_{\text{CC}}$$

where:

P_{add} = additional power dissipation (μW);

f_i = input frequency (MHz);

t_r = input rise time (ns); 10 % to 90 %;

t_f = input fall time (ns); 90 % to 10 %;

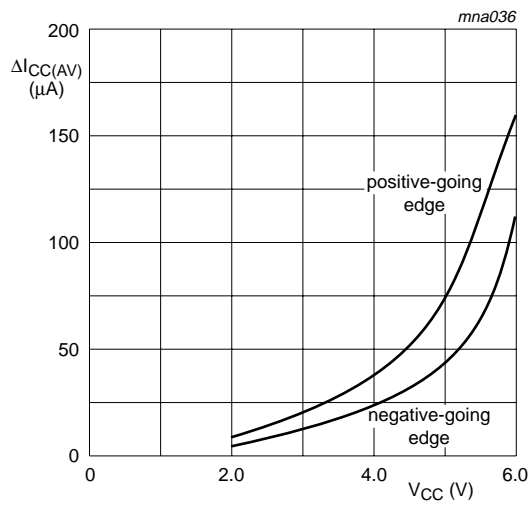
$\Delta I_{\text{CC(AV)}}$ = average additional supply current (μA).

$\Delta I_{\text{CC(AV)}}$ differs with positive or negative input transitions, as shown in [Figure 13](#).

For XC7WH14 used in relaxation oscillator circuit, see [Figure 14](#).

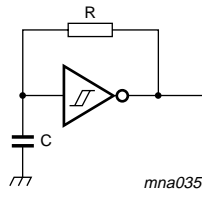
Note to the application information:

1. All values given are typical unless otherwise specified.



Linear change of V_I between $0.1V_{\text{CC}}$ to $0.9V_{\text{CC}}$

Fig 13. Average additional I_{CC}



$$f = \frac{1}{T} \approx \frac{1}{0.55 \times RC}$$

Fig 14. Relaxation oscillator using the XC7WH14

15. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

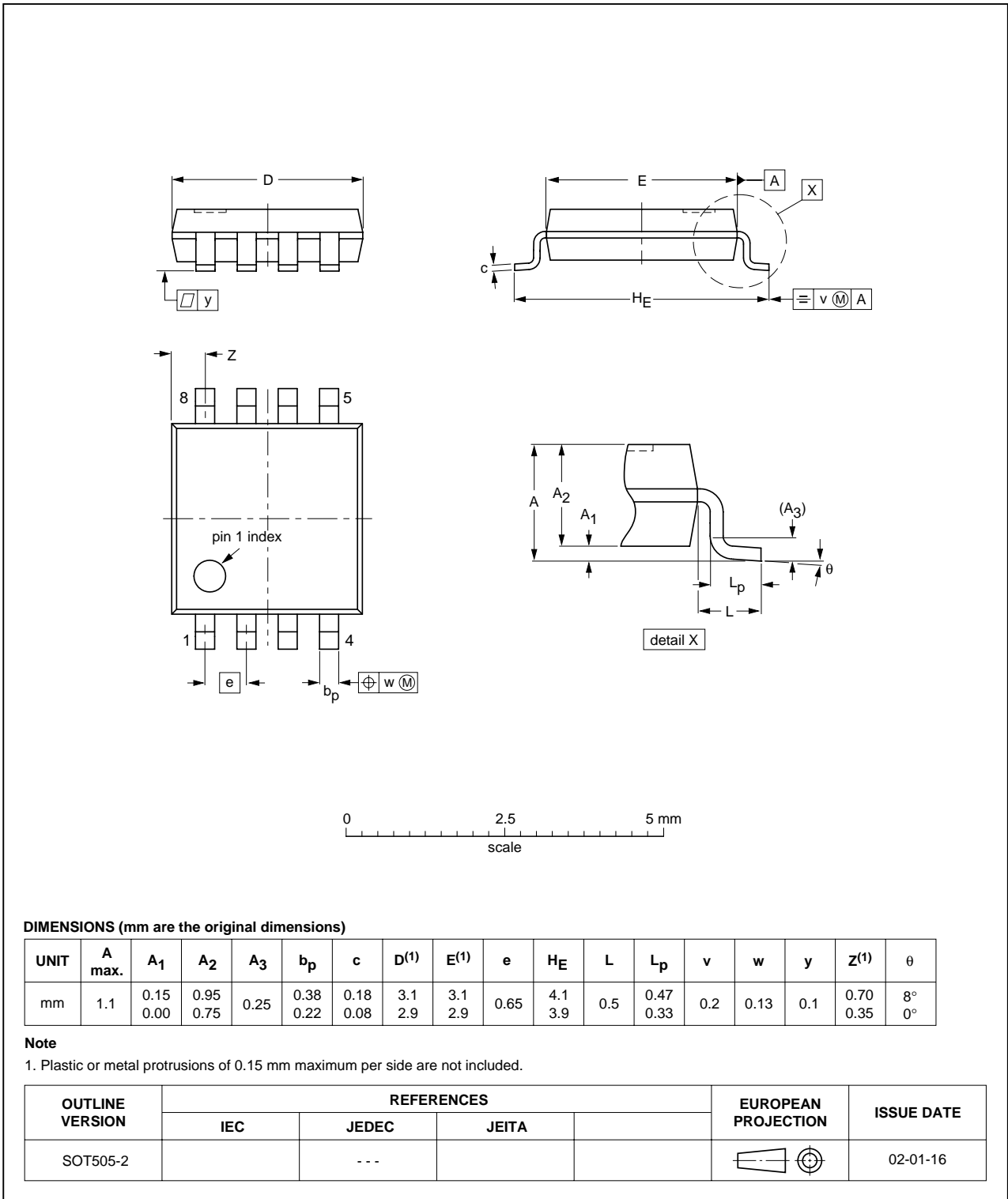


Fig 15. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

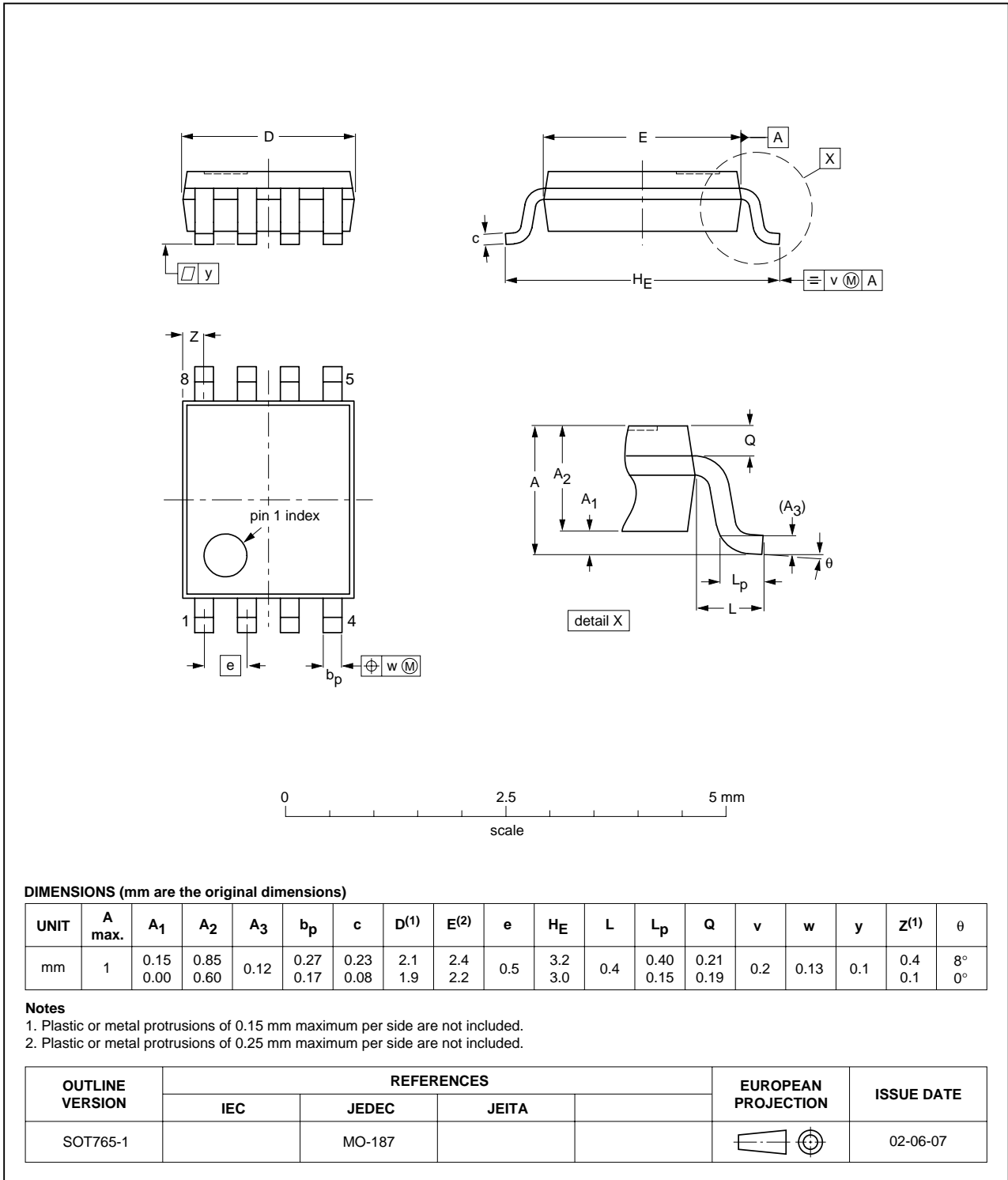


Fig 16. Package outline SOT765-1 (VSSOP8)

**XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm**

SOT996-2

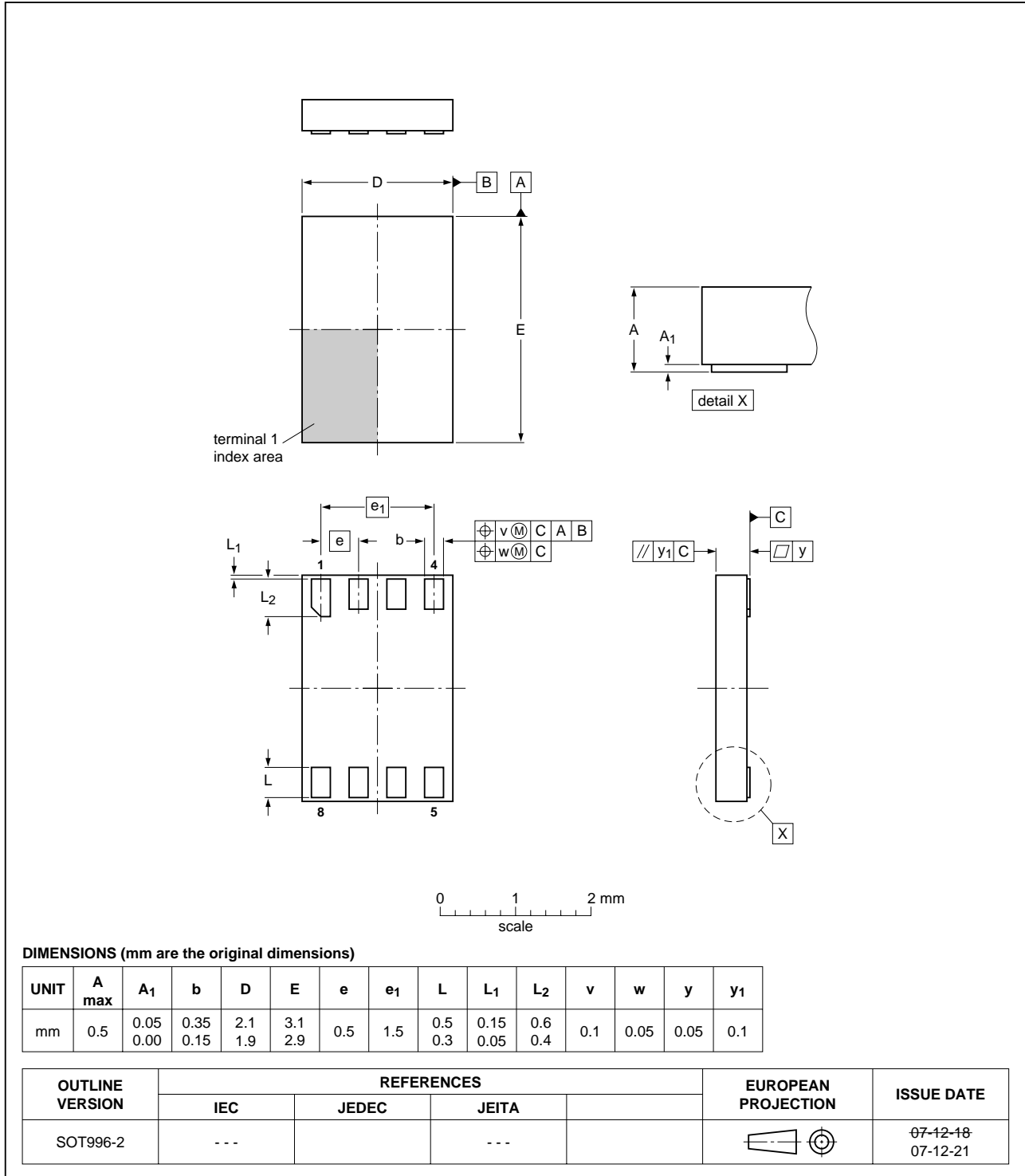


Fig 17. Package outline SOT996-2 (XSON8U)

16. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

17. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
XC7WH14_1	20090907	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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20. Contents

1 General description 1

2 Features 1

3 Applications 1

4 Ordering information 1

5 Marking 2

6 Functional diagram 2

7 Pinning information 2

7.1 Pinning 2

7.2 Pin description 3

8 Functional description 3

9 Limiting values 3

10 Recommended operating conditions 4

11 Static characteristics 4

11.1 Transfer characteristics 5

12 Dynamic characteristics 5

13 Waveforms 6

13.1 Transfer characteristic waveforms 7

14 Application information 9

15 Package outline 11

16 Abbreviations 14

17 Revision history 14

18 Legal information 15

18.1 Data sheet status 15

18.2 Definitions 15

18.3 Disclaimers 15

18.4 Trademarks 15

19 Contact information 15

20 Contents 16

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